



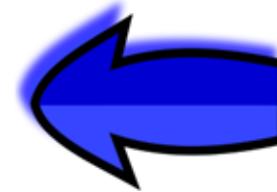
# **Chapter 7: A Primer On Digital Logic**

# **Basic Computer Architecture**



# Outline

- \* Transistors and Gates
- \* Combinational Logic
- \* Sequential Logic
- \* SRAM/ DRAM Cells



# Disclaimer: This chapter is only to get a high level overview ...



- \* We assume some **background** in logic gates, transistors, combinational and sequential logic
- \* The **aim** of this chapter is to only provide a high level overview
- \* For a **deeper** understanding consult any of the classic textbooks on digital logic

# Atoms and Molecules of Circuits

## The Transistor

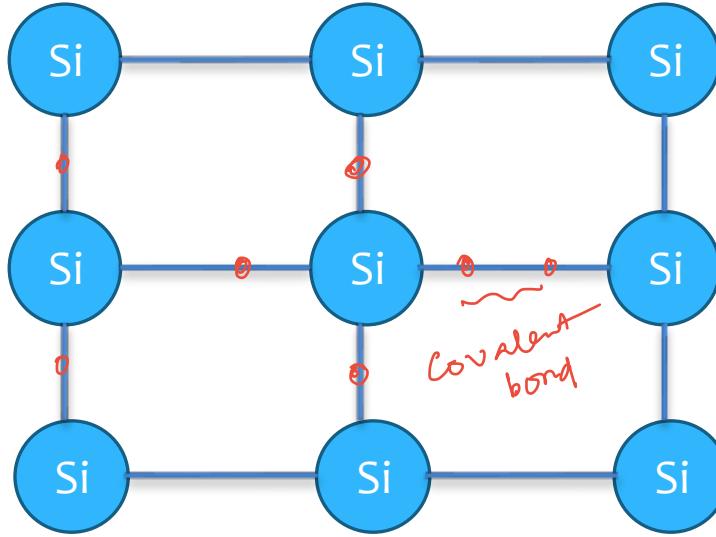


- It is just a **switch**.
- It is either switched **on** (current can flow), or switched **off** (no current flow)

# How is a Transistor Made?

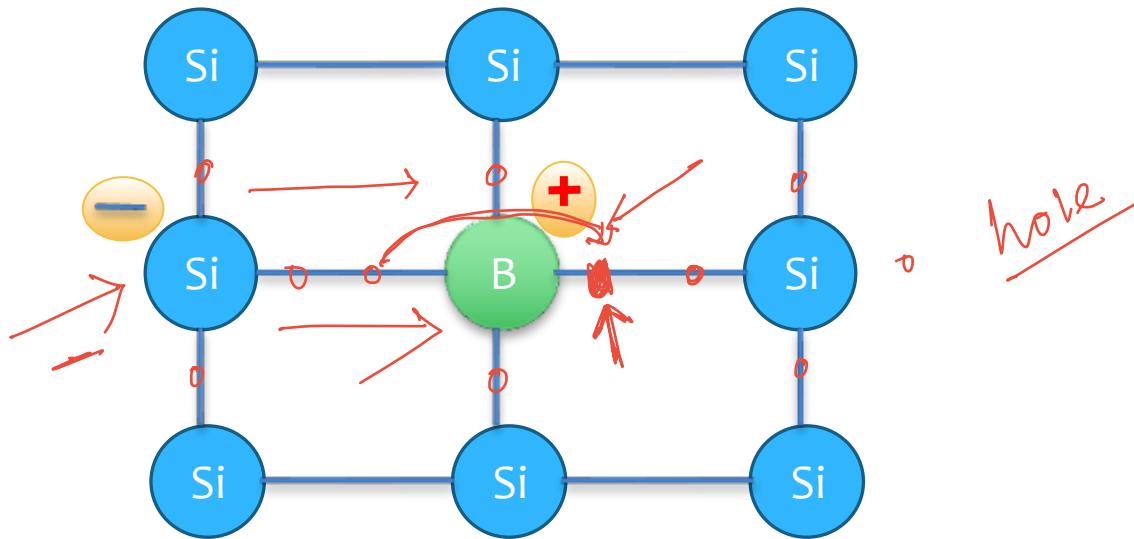
- \* It is made of **Silicon** ↗
  - \* Silicon is a semi-conductor (neither conductor or insulator).
  - \* We can change its properties:
  - \* Add a little bit of impurities → **doping**
- \* Dope it with Group III elements (3 valence electrons)
  - \* Boron, Aluminum and Gallium
  - \* It is called a **p-type** semiconductor
- \* Or, dope it with Group V elements (5 valence electrons)
  - \* Phosphorus or Arsenic
  - \* It is called a **n-type** semiconductor

# Silicon Lattice



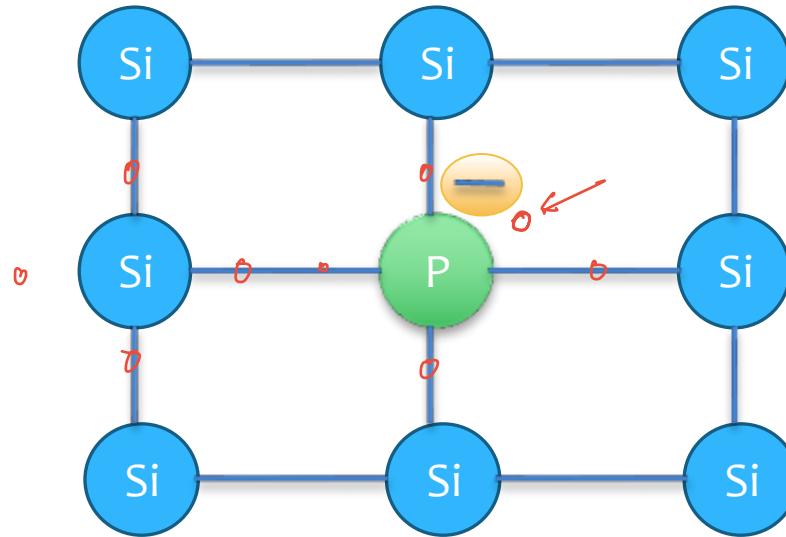
- \* This is a typical silicon lattice. Each Si atom is connected to 4 other atoms via covalent bond

# P-Type Doping



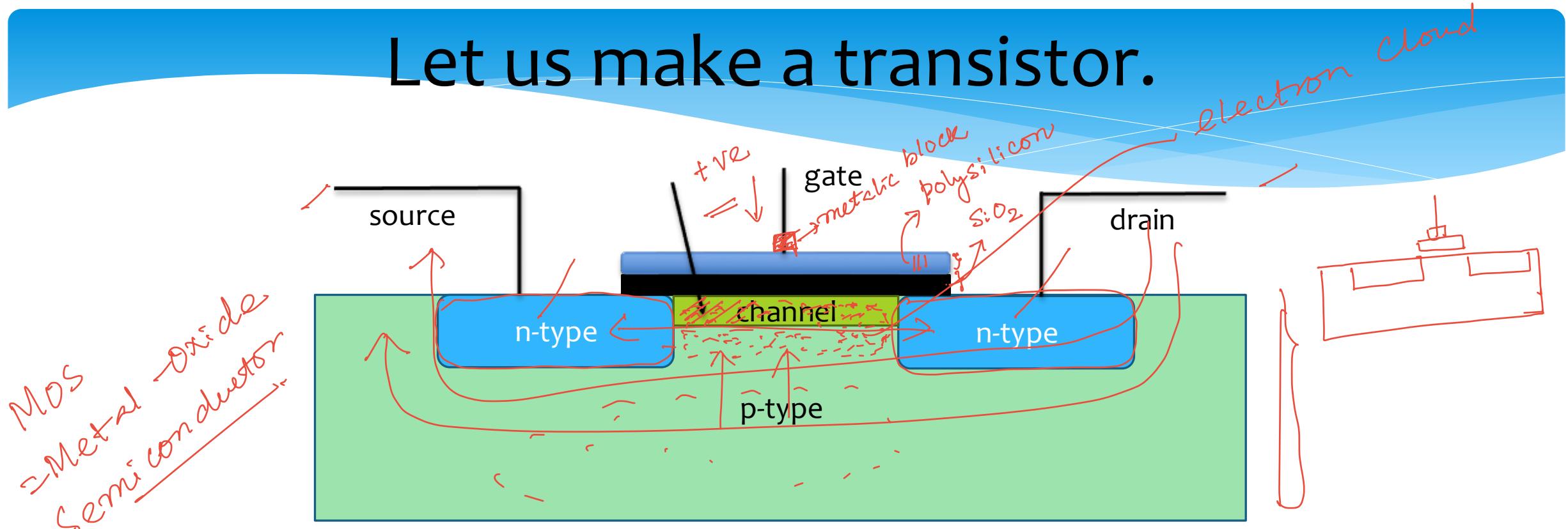
- \* If there is a Boron atom in the **lattice**. It will create bonds with the rest of the atoms.
- \* There will be one less electron (**hole**)
- \* Holes can **flow**. They are associated with +ve charge. (see the animation)

# N-Type Doping



- \* If there is a Phosphorus atom in the **lattice**. It will create bonds with the rest of the atoms.
- \* There will be one more electron (**electron**)
- \* Electrons can **flow**. They are associated with -ve charge. (see the animation)

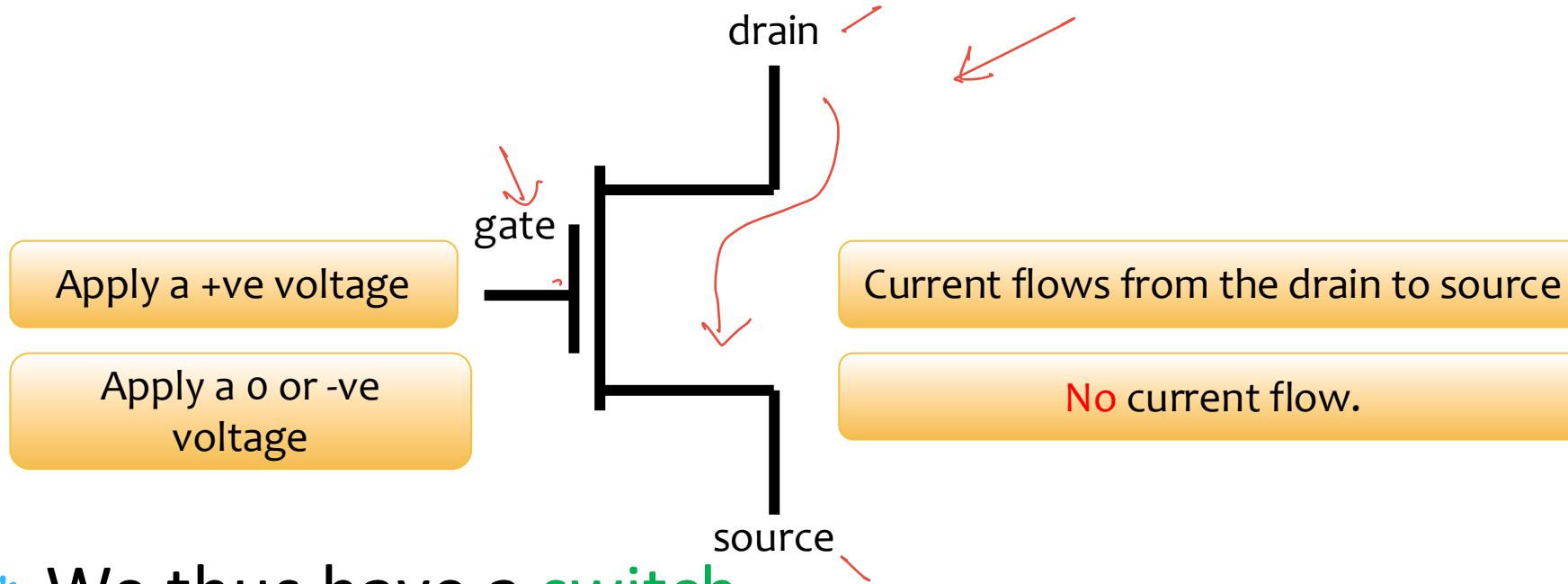
# Let us make a transistor.



- \* NMOS transistor → Put two **n-type** wells in a **p-type** substrate
- \* Now, assume that we apply **+ve** charge to the gate.
- \* Channel → This forms because electrons move towards the positive charge. Forms a conductive layer that can conduct **current**.

# NMOS Transistor

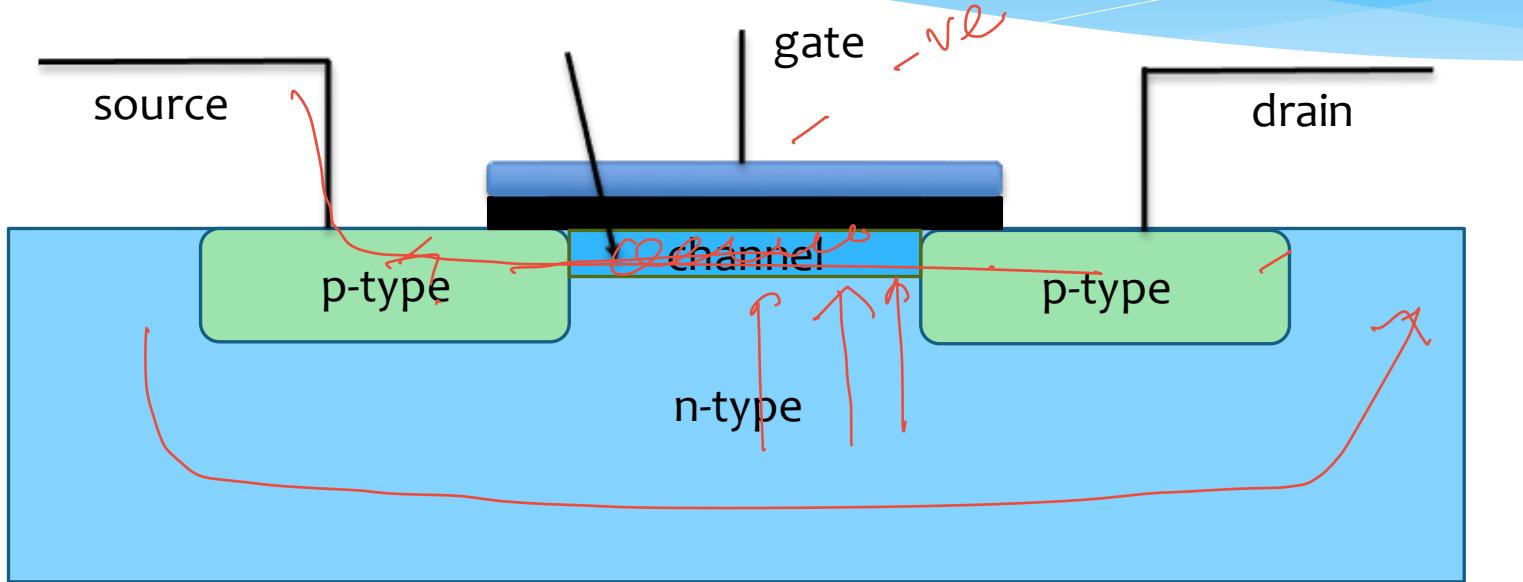
Metal-Oxide-Semiconductor



\* We thus have a **switch**

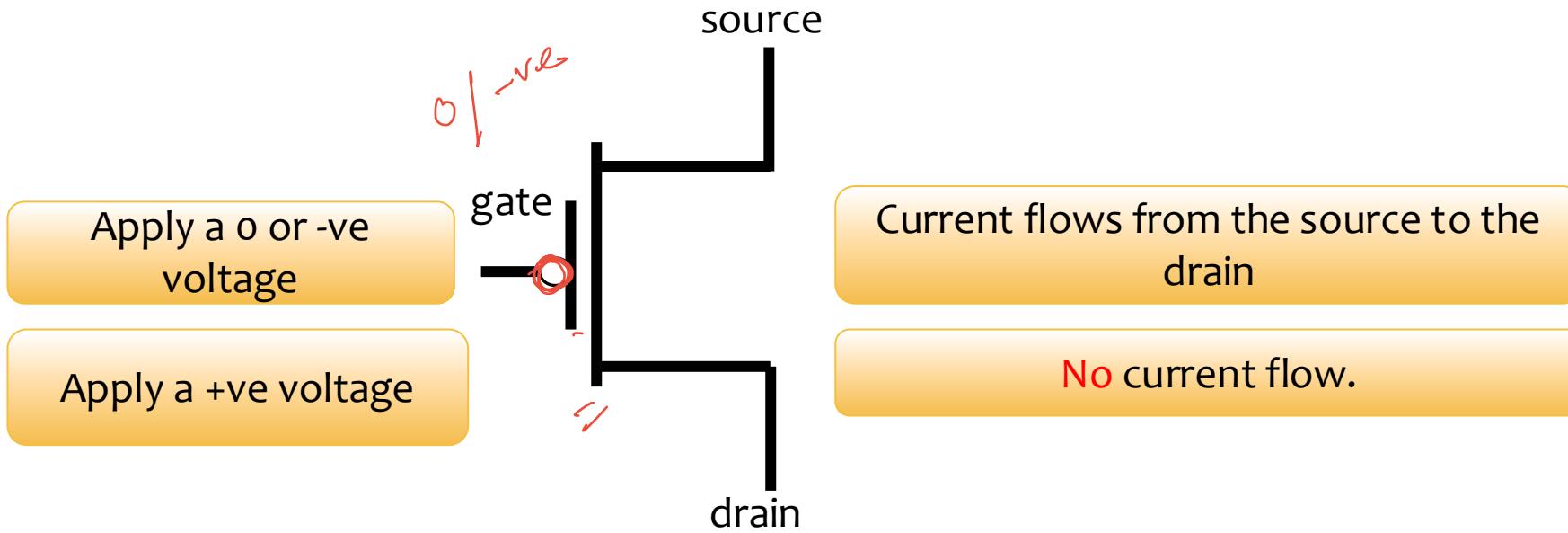
- \* Apply a **+ve** voltage at the gate → make the transistor conduct
- \* Apply a **-ve** or 0 voltage at the gate → transistor is off (no current flow across it)

# PMOS Transistor



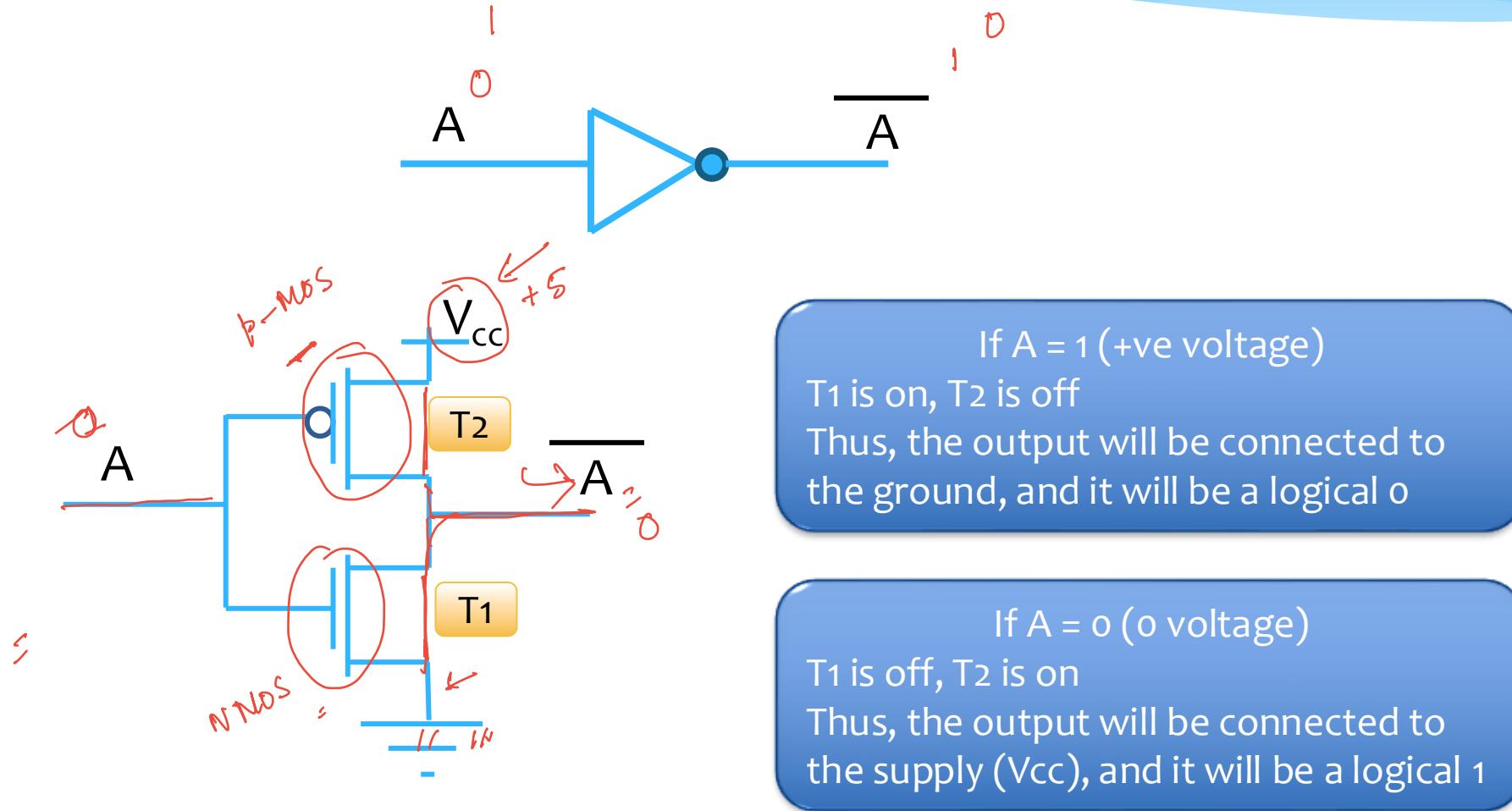
- \* PMOS transistor → Put two **p-type** wells in an **n-type** substrate
- \* Now, assume we apply **0 or -ve** charge to the gate.
- \* Channel → This forms because holes move towards the gate. This channel can conduct **current**.

# PMOS Transistor



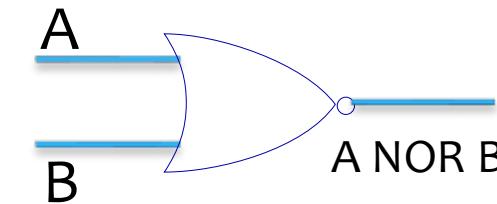
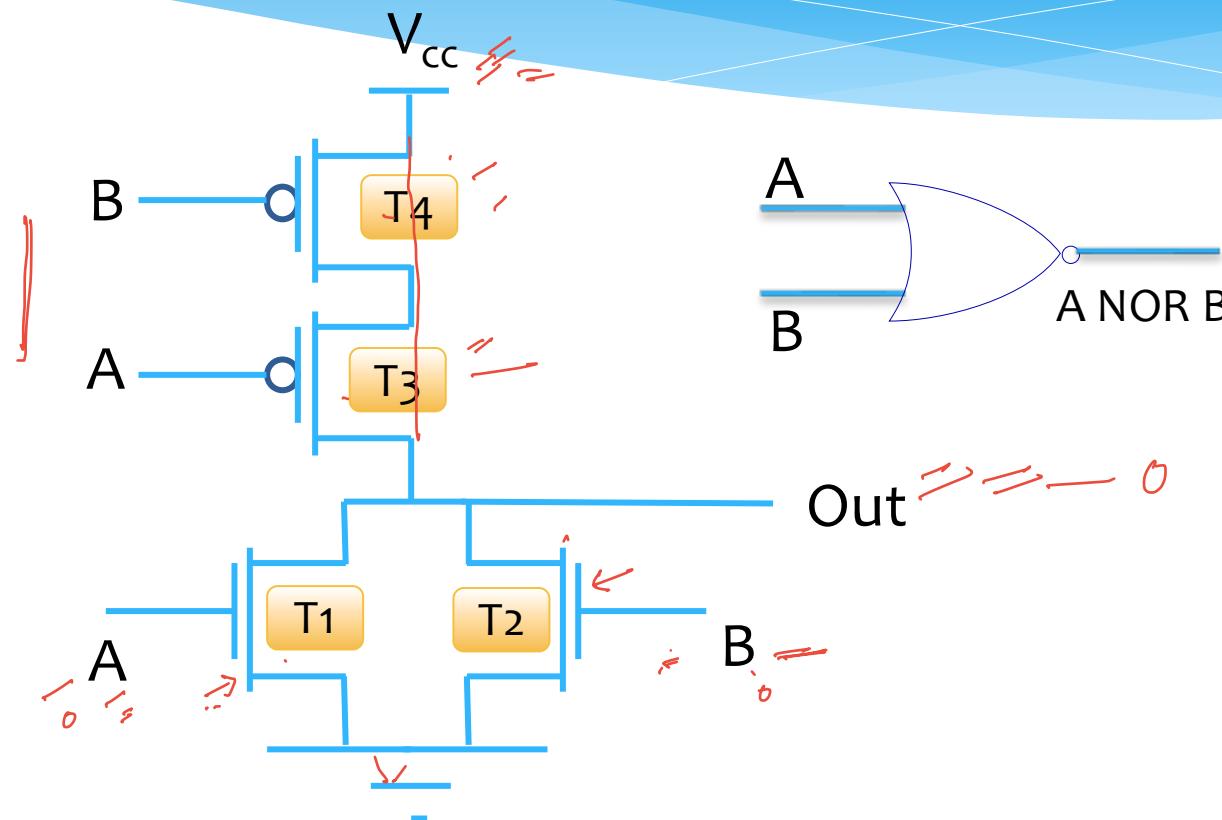
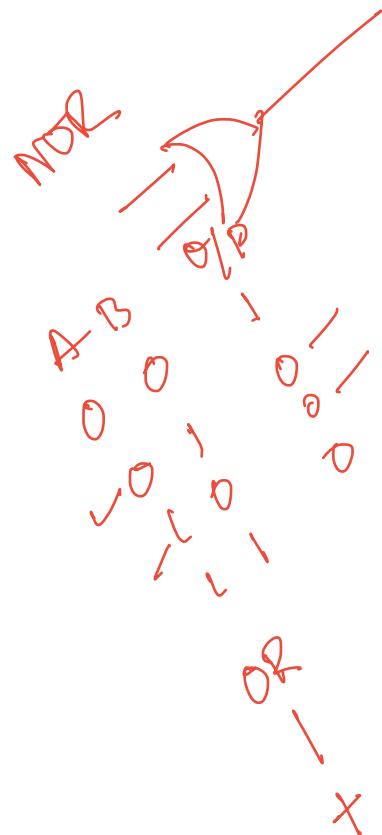
- \* We thus have a **switch**
  - \* Apply a **+ve** voltage at the gate → transistor is off (no current flow across it)
  - \* Apply a **-ve** or 0 voltage at the gate →transistor conducts

# Let us make an inverter



Complementary Metal-Oxide-Semiconductor

# NOR Gate



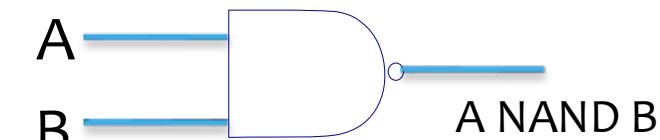
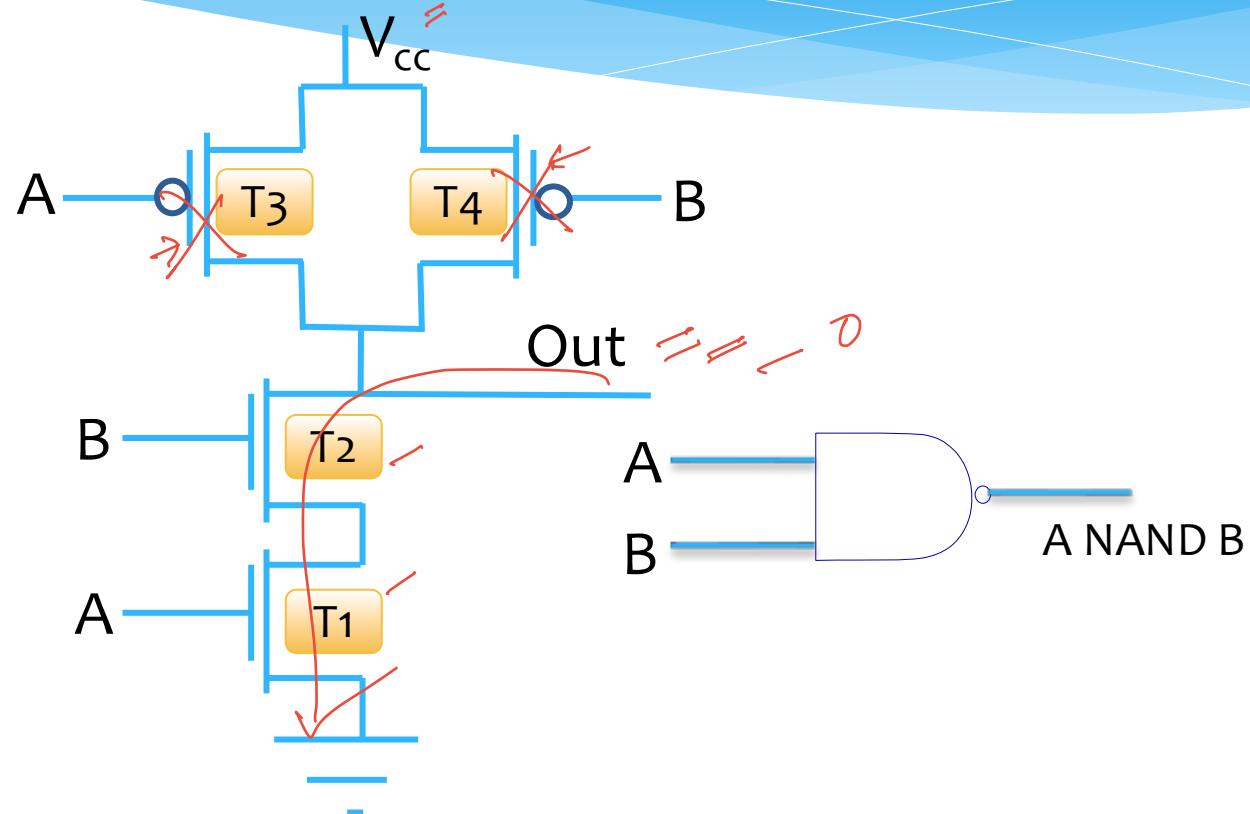
A	B	T1	T2	T3	T4	Out
0	0	off	off	on	on	1
1	0	on	off	off	on	0
0	1	off	on	on	off	0
1	1	on	on	off	off	0

NAND

O/P

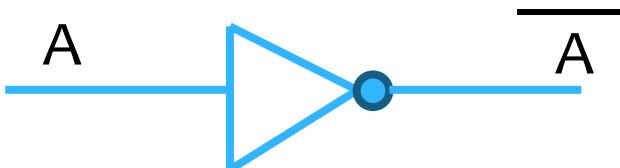
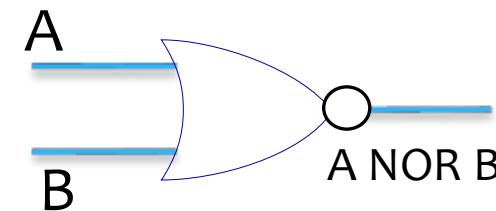
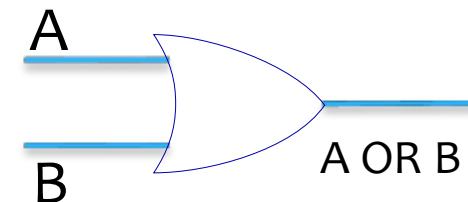
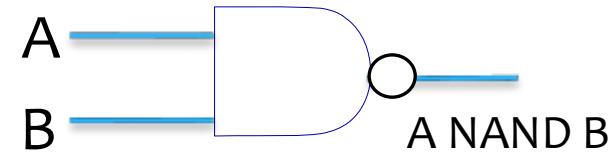
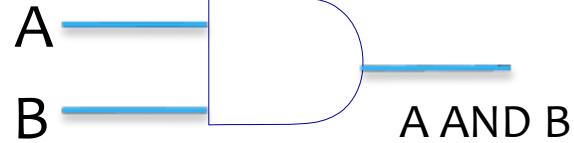
A	B	O/P
0	0	1
0	1	1
1	0	1
1	1	0

# NAND Gate



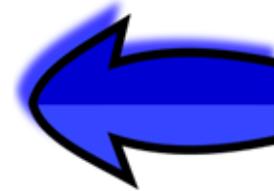
A	B	T1	T2	T3	T4	Out
0	0	off	off	on	on	1 ✓
1	0	on	off	off	on	1 ✓
0	1	off	on	on	off	1 ✓
1	1	on	on	off	off	0

# Summary of Logic Gates



# Outline

- \*Transistors and Gates
- \*Combinational Logic
- \* Sequential Logic
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# Multiplexer

Given  $n$  inputs, choose one based on the select bits.

Example: Given 8 inputs, 3 select bits, choose 1 among them

